WR0459I ṂṂÞ QSQ ÆṀч s ll ㄱ Silicon NPN transistor in a TO-126F Plastic Package.

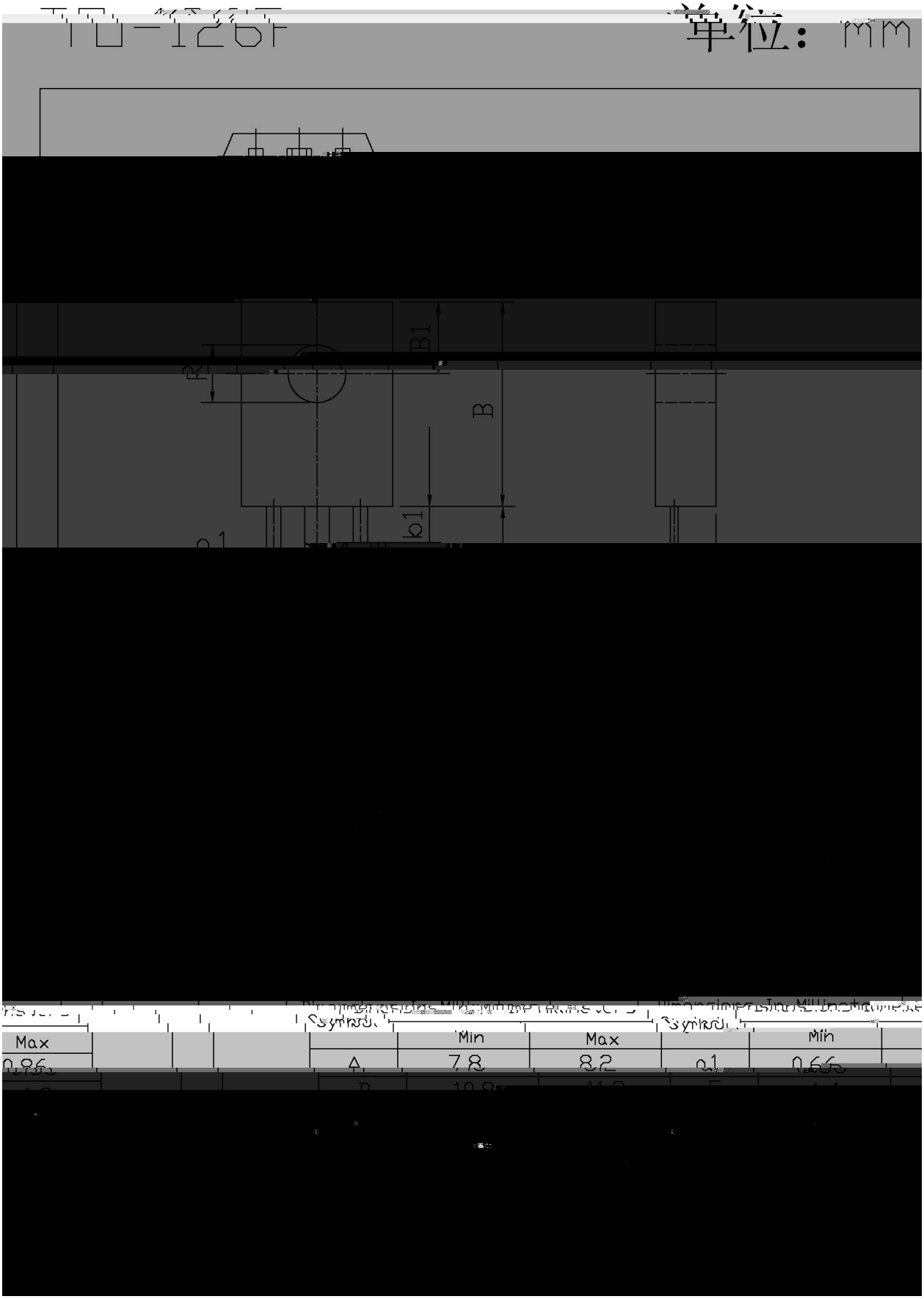
ǎ я ㄡ/Hυ ᵍ ll ڑ ɔ ķ ņ
High V_{CEO}

/ Absolute Maximum Ratings(Ta=25)

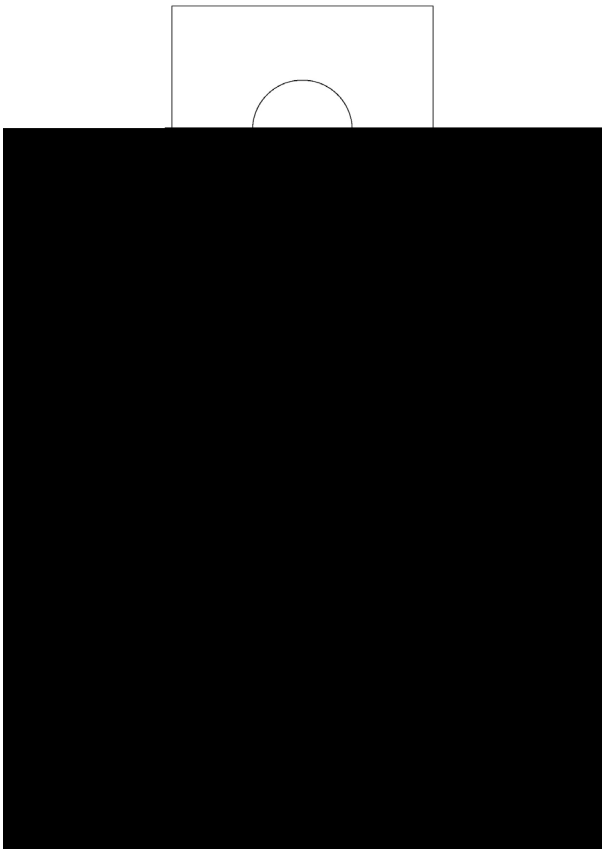
v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	100	mA
Collector Current – Continuous(Pulse)	I_{CP}	200	mA
Collector Power Dissipation	P_C	1.2	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω Parameter	ϒ N Symbol	Ш ː ϳ Ţ Test Conditions	ώ ṇ Ö Min	Ɛ ʒ Ö Typ	ώ ² Ö Max	D Ч Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=10μA I_E=0	300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=0.1mA I_B=0	300			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=10μA I_C=0	7.0			V
DC Current Gain	h_{FE}	V_{CE}=50V I_C=5.0mA	50		250	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=30mA I_B=3.0mA			1.5	V
Base to Emitter Voltage	V_{BE}	V_{CE}=10V I_C=30mA			1.2	V
Transition Frequency	f_T	V_{CB}=30V I_C=20mA	70	140		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=30V I_E=0 f=1.0MHz		2.4		pF

/ Package Dimensions



/ Marking Instructions



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EU χ

F6396 χ

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Note:

BR:	Company Code
C3063:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ẙ 25 Ḱ 150 ɬ ı ̀H ژ 60 Ḱ 90sec;

2 Š Ө □ ẙ 255 ° 5 ɬ ı ̀H ژ ̀Y ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ﾙ ↄ ▸ ẙ ㎛ 2 Ḱ 10 ɬ /sec

5 Ù Ẽ в ц 25

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

P8358SPEC. (Cooling